

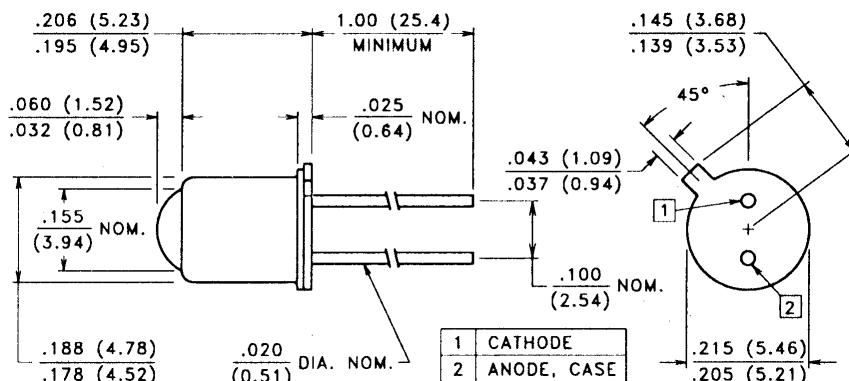
GaAs Infrared Emitting Diodes

TO-46 Lensed Package — 940 nm

VTE1113H



PACKAGE DIMENSIONS inch (mm)



CASE 24 TO-46 HERMETIC (Lensed)
CHIP SIZE: .018" X .018"

DESCRIPTION

This narrow beam angle TO-46 hermetic emitter contains a large area, double wirebonded, GaAs, 940 nm IRED chip suitable for higher current pulse applications.

RoHS Compliant



ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures			Maximum Reverse Voltage:	5.0V
Storage and Operating:	-55°C to 125°C		Maximum Reverse Current @ $V_R = 5V$:	10 μA
Continuous Power Dissipation:	200 mW		Peak Wavelength (Typical):	940 nm
Derate above 30°C:	2.11 mW/°C		Junction Capacitance @ 0V, 1 MHz (Typ.):	35 pF
Maximum Continuous Current:	100 mA		Response Time @ $I_F = 20$ mA	
Derate above 30°C:	1.05 mA/°C		Rise: 1.0 μs Fall: 1.0 μs	
Peak Forward Current, 10 μs , 100 pps:	3.0 A		Lead Soldering Temperature:	260°C
Temp. Coefficient of Power Output (Typ.):	-8%/°C		(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 123-124)

Part Number ■	Output							Forward Drop		Half Power Beam Angle
	Irradiance				Radiant Intensity	Total Power	Test Current	V _F		
	E _e		Condition		I _e	P _O	I _{FT}	@ I _{FT}		θ _{1/2}
	mW/cm ²		distance	Diameter	mW/sr	mW	mA (Pulsed)	Volts		Typ.
	Min.	Typ.	mm	mm	Min.	Typ.		Typ.	Max.	
VTE1113H	12	15	36	6.4	156	30	1.0	1.9	2.5	±10°

■ Refer to General Product Notes, page 2.